

ABSTRACT OF THE DISCLOSURE

An interlayer insulating film is formed on a semiconductor substrate. An intra-layer insulating film is formed on the interlayer film. A recess is formed through the intra-layer film. The recess has a pad-part and a wiring-part 5 continuous with the pad-part. The pad-part is wider than the width of the wiring-part. Convex regions are left in the pad-part. The convex regions are disposed in such a manner that a recess area ratio in a near wiring area superposed upon an extended area of the wiring-part into the pad-part, within a first frame area having as an outer periphery an outer periphery of the pad-part and having a first 10 width, becomes larger than a recess area ratio in a second frame area having as an outer periphery an inner periphery of the first frame area and having a second width. A conductive film is filled in the recess.

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